COMPLIANT





# 700 MHz, -3 dB Bandwidth; Dual SPDT Analog Switch

### **DESCRIPTION**

DG2723 is a low  $R_{ON}$ , high bandwidth analog switch configured in dual SPDT. It achieves 5.5  $\Omega$  switch on resistance, greater than 700 MHz -3 dB bandwidth with 5 pF load, and a channel to channel crosstalk at -36 dB and isolation at -29 dB. Fabricated with high density sub micro CMOS process, the DG2723 provides low parasitic capacitance, handles bidirectional signal flow with minimized phase distortion. Guaranteed 1.3 V logic high threshold makes it possible to interface directly with low voltage MCUs. The DG2723 is designed for a wide range of operating voltages from 2.7 V to 5.5 V that can be driven directly from one cell Li-ion battery. On-chip protection circuit protects again fault events when signals at "com" pins goes beyond V+.

Latch up current is 500 mA, as per JESD78, and its ESD tolerance exceeds 5 kV. Packaged in ultra small miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm), it is ideal for portable high speed mix signal switching application. As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device termination. The miniQFN-10 package has a nickel-palladium-gold device termination and is represented by the lead (Pb)-free "-E4" suffix to the ordering part number. The nickel-palladium-gold device terminations meet all JEDEC® standards for reflow and MSL rating. As a further sign of Vishay Siliconix's commitment, the DG2723 is fully RoHS-complaint.

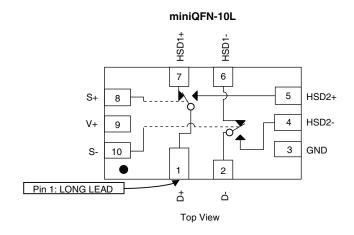
### **FEATURES**

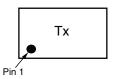
- Wide operation voltage range
- Low on-resistance, 5.5 Ω (typical at 3 V)
- Low capacitance, 5.6 pF (typical)
- -3 dB high bandwidth with 5 pF load: 700 MHz (typical)
- · Low bit to bit skew: 40 pS (typical)
- Low power consumption
- · Low logic threshold: V
- Power down protection: D+, D-, HSD1+, HSD1-, HSD2+, and HSD2- pins can tolerate up to 5.5 V when V+ = 0 V
- 5 kV ESD protection (HBM)
- Latch-up current 500 mA per JESD78
- Lead (Pb)-free low profile miniQFN-10 (1.4 mm x 1.8 mm x 0.55 mm)
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### **APPLICATIONS**

- · Cellular phones
- Portable media players
- PDA
- Digital camera
- GPS
- Notebook computer
- TV, monitor, and set top box

### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**





Device marking: Tx for DG2723 x = Date / Lot traceability code



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ORDERING INFORMATION		
TEMP. RANGE	PACKAGE	PART NUMBER
-40 °C to +85 °C	miniQFN-10	DG2723DN-T1-E4

TRUTH TABLE				
S+ (PIN 8)	S- (PIN 10)	FUNCTION		
Х	0	D- = HSD1-		
Х	1 D- = HSD2-			
0	X	D+ = HSD1+		
1	Х	D+ = HSD2+		

PIN DESCRIPTION			
PIN NAME	DESCRIPTION		
S+	Select input for D+		
S-	Select input for D-		
HSD±, HSD2±, D±	Data port		

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
PARAMETER		LIMIT	UNIT	
Deference to CND	V+, D±, HSD1±, HSD2±	-0.3 to+6	V	
Reference to GND	S+, S- <sup>a</sup>	-0.3 to (V+ + 0.3)	v	
Current (any terminal except S+, S-, D±	30			
Continuous current (S+, S-, D±, HSD1±, HSD2±)		± 250	mA	
Peak current (pulsed at 1 ms, 10 % duty cycle)		± 500		
Storage temperature (D suffix)		-65 to +150	°C	
Power dissipation (packages) b miniQFN-10 c		208	mW	
ESD (human body model)		5	kV	
Latch-up (current injection)		500	mA	

#### Notes

- a. Signals on S+, S-, exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- b. All leads welded or soldered to PC board
- c. Derate 2.6 mW/°C above 70 °C

SPECIFICATIONS (V+ = 3 V)									
PARAMETER	SYMBOL	TEST CONDITIONS OTHERWISE UNLESS SPECIFIED				LIMITS -40 °C to +85 °C MIN. b TYP. c MAX. b			UNIT
Analog Switch					L		ı		
Analog signal range d	V <sub>ANALOG</sub>	R <sub>DS(on)</sub>	Full	0	-	V+	V		
On-resistance	Boo.	$V+ = 3 \text{ V}, I_{D+} = 8 \text{ mA}, V_{HSD1/2+} = 0.4 \text{ V}$	Room	-	5.5	8			
On-resistance	R <sub>DS(on)</sub>	$V + = 3 V$ , $ID_{\pm} = 0 IIIA$ , $V_{HSD1/2\pm} = 0.4 V$	Full	-	-	9			
On-resistance match <sup>d</sup>	$\Delta R_{ON}$	V+ = 3 V, $I_{D\pm}$ = 8 mA, $V_{HSD1/2\pm}$ = 0.4 V	Room	-	0.8	1	Ω		
On-resistance resistance flatness <sup>d</sup>	R <sub>ON</sub> Flatness	$V+ = 3 V$ , $I_{D\pm} = 8 mA$ , $V_{HSD1/2\pm} = 0 V$ , 1 V	Room	-	2	-			
Switch off leakage current	I <sub>(off)</sub>	$V+ = 4.3 \text{ V}, V_{\text{HSD1/2}\pm} = 0.3 \text{ V}, 3 \text{ V}, V_{\text{D}\pm} = 3 \text{ V}, 0.3 \text{ V}$		-100	-	100	^		
Channel on leakage current	I <sub>(on)</sub>	$V+ = 4.3 \text{ V}, V_{HSD1/2\pm} = 0.3 \text{ V}, 4 \text{ V}, \ V_{D\pm} = 4 \text{ V}, 0.3 \text{ V}$	Full	-200	-	200	nA		
Digital Control									
Input voltage high	V	V+ = 3 V to 3.6 V	Full	1.3	-	-			
Input voltage high	V <sub>INH</sub>	V+ = 4.3 V	Full	1.5	-	-	V		
Input voltage low	V <sub>INL</sub>	V+ = 3 V to 4.3 V	Full	-	-	0.5			
Input capacitance	C <sub>IN</sub>			-	6.5	-	pF		
Input current	I <sub>INL</sub> or I <sub>INH</sub>	$V_{IN} = 0$ or $V+$	Full	-1	-	1	μΑ		



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SPECIFICATIONS (V+ = 3 V)								
PARAMETER	SYMBOL TEST CONDITIONS OTHERWISE UNLESS SPECIFIED		TEMP.a	LIMITS -40 °C to +85 °C			ns pC dB MHz pF	UNIT
		OTHERWISE UNLESS SPECIFIED		MIN. b	TYP. c	MAX. b		
Dynamic Characteristics								
Break-before-make time e, d	t <sub>BBM</sub>		Room	_	5	_		
Break before make time	-RRM		Full		0	-		
S-, S+ turn-on time <sup>e, d</sup>	t <sub>ON</sub>	$V+ = 3 V$ , $V_{D1/2\pm} = 1.5 V$ , $R_L = 50 \Omega$ ,	Room	_		30		
o, of tain on time	ON	$C_L = 35 \text{ pF}$	Full			30	113	
S-, S+ turn-off time e, d	t <sub>OFF</sub>		Room	_	_	25		
o, o+ tain on time	UFF		Full			20		
Charge injection <sup>d</sup>	$Q_{INJ}$	$C_L = 1 \text{ nF}, R_{GEN} = 0 \Omega, V_{GEN} = 0 V$		-	3	ı	рC	
Off-isolation <sup>d</sup>	OIRR	$V+ = 3 V \text{ to } 3.6 V, R_L = 50 \Omega, C_L = 5 pF,$		-	-29	ı	dВ	
Crosstalk <sup>d</sup>	X <sub>TALK</sub>	f = 240 MHz		-	-36	ı	uБ	
Bandwidth <sup>d</sup>	BW	V+ = 3 V to 3.6 V, $C_L$ = 5 pF, $R_L$ = 50 $\Omega$ , -3 dB		-	700	ı	MHz	
Channel-off capacitance d	C <sub>D1± (off)</sub>	V+ = 3.3 V, f = 1 MHz	Room	-	2.5	ı	nE	
Charinei-on capacitance -	$C_{D2\pm  (off)}$			-	2.5	ı		
Channel-on capacitance d	$C_{D\pm \text{ (off)}}$	V+ = 3.3 V, T = T WIT12	1100111	-	2.5	ı	ρι	
Charmer-on capacitance	$C_{D\pm (on)}$			-	6.5	ı		
Channel-to-channel skew <sup>d</sup>	t <sub>SK(O)</sub>			-	50	ı		
Skew off opposite transitions of the same output <sup>d</sup>	t <sub>SK(p)</sub>	$V+ = 3 V \text{ to } 3.6 V, R_L = 50 \Omega, C_L = 5 pF$		-	20	-	ps	
Total jitter <sup>d</sup>	tJ			-	200	-		
Power Supply								
Power supply range	V+			2.6	-	5.5	V	
Power supply current	l+	$V_{IN} = 0 V$ , or V+	Full	-	-	2	μΑ	

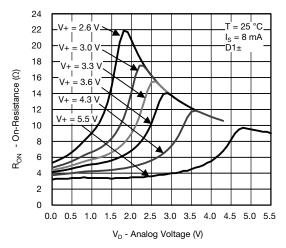
### Notes

- a. Room = 25 °C, Full = as determined by the operating suffix
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- c. Typical values are for design aid only, not guaranteed nor subject to production testing
- d. Guarantee by design, not subjected to production test
- e. V<sub>IN</sub> = input voltage to perform proper function
- f. Crosstalk measured between channels

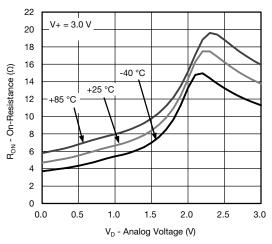
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



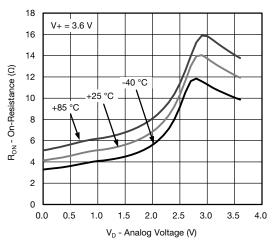
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



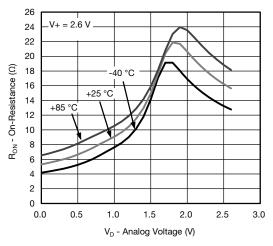
R<sub>ON</sub> vs. V<sub>D</sub> and Single Supply Voltage



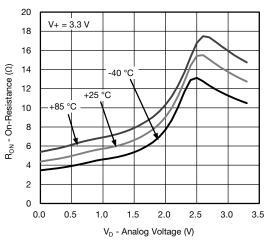
R<sub>ON</sub> vs. Analog Voltage and Temperature



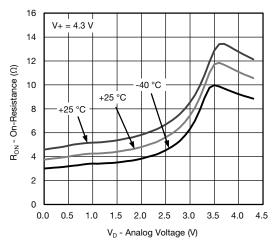
R<sub>ON</sub> vs. Analog Voltage and Temperature



R<sub>ON</sub> vs. Analog Voltage and Temperature



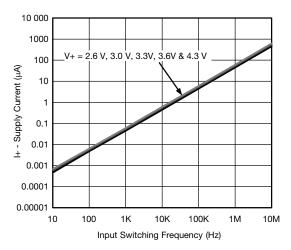
R<sub>ON</sub> vs. Analog Voltage and Temperature



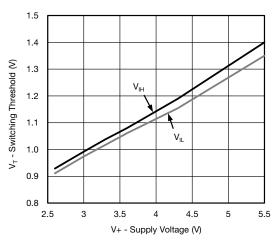
R<sub>ON</sub> vs. Analog Voltage and Temperature



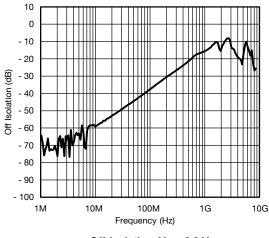
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



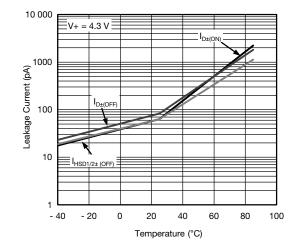
#### **Supply Current vs. Input Switching Frequency**



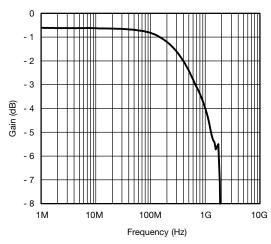
Switching Threshold vs. Supply Voltage



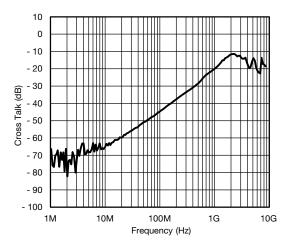
Off-Isolation, V+ = 3.3 V



Leakage Current vs. Temperature



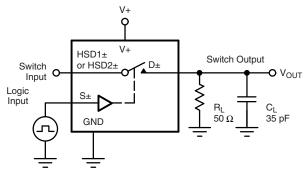
Gain vs. Frequency, V+ = 3.3 V



Crosstalk, V+ = 3.3 V

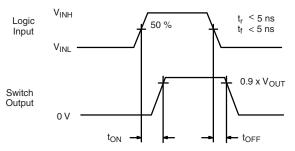


### **TEST CIRCUITS**



C<sub>L</sub> (includes fixture and stray capacitance)

$$V_{OUT} = D \pm \left( \frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch on Logic input waveforms inverted for switches that have the opposite logic sense.

Fig. 1 - Switching Time

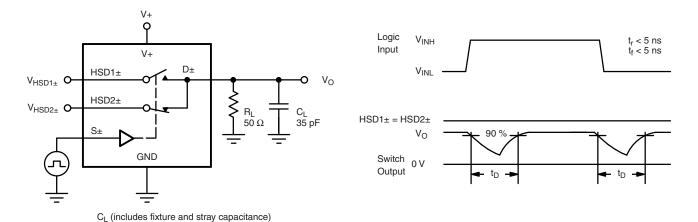


Fig. 2 - Break-Before-Make Interval

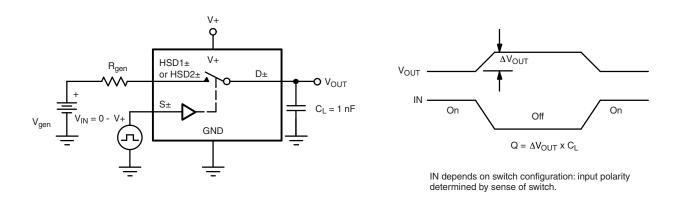


Fig. 3 - Charge Injection



## **TEST CIRCUITS**

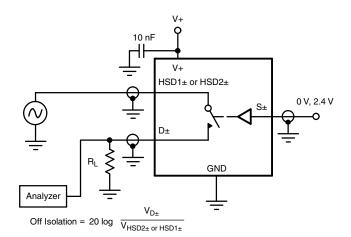


Fig. 4 - Off-Isolation

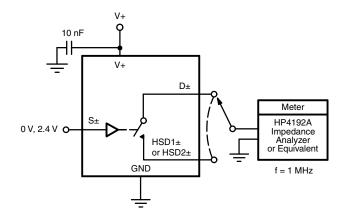


Fig. 5 - Channel Off/On Capacitance



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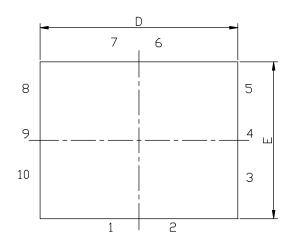
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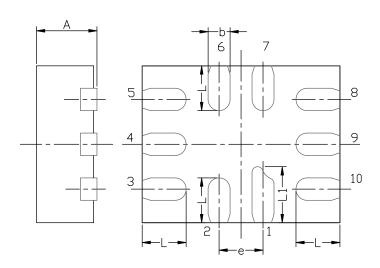
PRODUCT SUMMARY		
Part number	DG2723	
Status code	2	
Configuration	SPDT x 2	
Single supply min. (V)	2.6	
Single supply max. (V)	5.5	
Dual supply min. (V)	-	
Dual supply max. (V)	-	
On-resistance (Ω)	5.5	
Charge injection (pC)	3	
Source on capacitance (pF)	6.5	
Source off capacitance (pF)	2.5	
Leakage switch on typ. (nA)	-	
Leakage switch off max. (nA)	100	
-3 dB bandwidth (MHz)	700	
Package	miniQFN-10	
Functional circuit / applications	Multi purpose, USB, portable	
Interface	Binary	
Single supply operation	Yes	
Dual supply operation	-	
Turn on time max. (ns)	30	
Crosstalk and off isolation	-36	

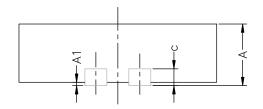
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?68767">www.vishay.com/ppg?68767</a>.

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# MINI QFN-10L CASE OUTLINE







DIM -		MILLIMETERS		INCHES			
	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.	
Α	0.45	0.55	0.60	0.0177	0.0217	0.0236	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С		0.150 or 0.127 REF <sup>(1)</sup>			0.006 or 0.005 REF (1	)	
D	1.70	1.80	1.90	0.067 0.071 0		0.075	
E	1.30	1.40	1.50	0.051	0.055	0.059	
е		0.40 BSC			0.016 BSC		
L	0.35	0.40	0.45	0.014	0.016	0.018	
L1	0.45	0.50	0.55	0.0177	0.0197	0.0217	

### Note

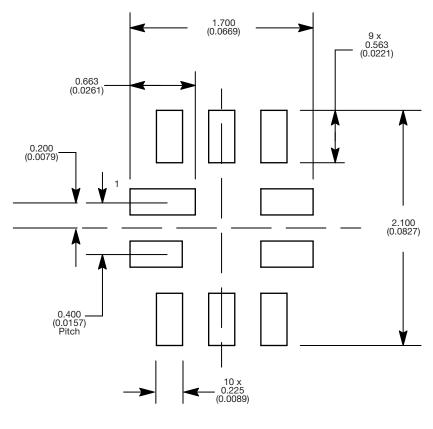
ECN T16-0163-Rev. B, 16-May-16 DWG: 5957

<sup>(1)</sup> The dimension depends on the leadframe that assembly house used.



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## **RECOMMENDED MINIMUM PADS FOR MINI QFN 10L**



Mounting Footprint Dimensions in mm (inch)



# **Legal Disclaimer Notice**

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